

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

CoolMOS™ C6

600V CoolMOS™ C6 Power Transistor
IPx60R099C6

Data Sheet

Rev. 2.3
Final

600V CoolMOS™ C6 Power Transistor

IPA60R099C6, IPB60R099C6
IPP60R099C6 IPW60R099C6

1 Description

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ C6 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The offered devices provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter, and cooler.

Features

- Extremely low losses due to very low FOM $R_{DS(on)} \cdot Q_g$ and E_{oss}
- Very high commutation ruggedness
- Easy to use/drive
- JEDEC¹⁾ qualified, Pb-free plating, Halogen free

Applications

PFC stages, hard switching PWM stages and resonant switching PWM stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom and UPS.

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

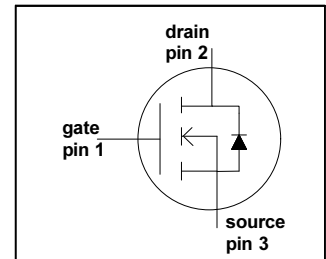
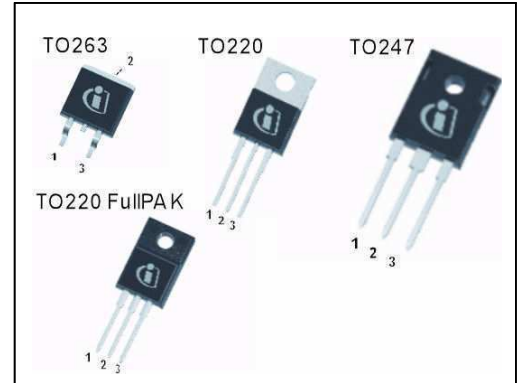


Table 1 Key Performance Parameters

| Parameter | Value | Unit |
|----------------------|-------|------------|
| $V_{DS} @ T_{j,max}$ | 650 | V |
| $R_{DS(on),max}$ | 0.099 | Ω |
| $Q_{g,typ}$ | 119 | nC |
| $I_{D,pulse}$ | 112 | A |
| $E_{oss} @ 400V$ | 9.3 | μJ |
| Body diode di/dt | 300 | A/ μs |

| Type / Ordering Code | Package | Marking | Related Links |
|----------------------|------------------|---------|---|
| IPW60R099C6 | PG-TO247 | 6R099C6 | IFX C6 Product Brief IFX C6 Portfolio IFX CoolMOS Webpage IFX Design tools |
| IPB60R099C6 | PG-TO263 | | |
| IPP60R099C6 | PG-TO220 | | |
| IPA60R099C6 | PG-TO220 FullPAK | | |

1) J-STD20 and JESD22

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2 Maximum ratings

at $T_j = 25\text{ °C}$, unless otherwise specified.

Table 2 Maximum ratings

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|---|----------------|--------|------|------|------------|---|
| | | Min. | Typ. | Max. | | |
| Continuous drain current ¹⁾ | I_D | - | - | 37.9 | A | $T_C = 25\text{ °C}$ |
| | | | | 24 | | $T_C = 100\text{ °C}$ |
| Pulsed drain current ²⁾ | $I_{D,pulse}$ | - | - | 112 | A | $T_C = 25\text{ °C}$ |
| Avalanche energy, single pulse | E_{AS} | - | - | 796 | mJ | $I_D = 6.6\text{ A}, V_{DD} = 50\text{ V}$ (see table 21) |
| Avalanche energy, repetitive | E_{AR} | - | - | 1.2 | | $I_D = 6.6\text{ A}, V_{DD} = 50\text{ V}$ |
| Avalanche current, repetitive | I_{AR} | - | - | 6.6 | A | |
| MOSFET dv/dt ruggedness | dv/dt | - | - | 50 | V/ns | $V_{DS} = 0 \dots 480\text{ V}$ |
| Gate source voltage | V_{GS} | -20 | - | 20 | V | static |
| | | -30 | | 30 | | AC ($f > 1\text{ Hz}$) |
| Power dissipation for TO-220, TO-247, TO-263 | P_{tot} | - | - | 278 | W | $T_C = 25\text{ °C}$ |
| Power dissipation for TO-220 FullPAK | P_{tot} | - | - | 35 | | |
| Operating and storage temperature | T_j, T_{stg} | -55 | - | 150 | °C | |
| Mounting torque TO-220, TO-247 | | - | - | 60 | Ncm | M3 and M3.5 screws |
| Mounting torque TO-220 FullPAK | | | | 50 | | M2.5 screws |
| Continuous diode forward current | I_S | - | - | 33 | A | $T_C = 25\text{ °C}$ |
| Diode pulse current ²⁾ | $I_{S,pulse}$ | - | - | 112 | A | $T_C = 25\text{ °C}$ |
| Reverse diode dv/dt ³⁾ | dv/dt | - | - | 15 | V/ns | $V_{DS} = 0 \dots 400\text{ V}, I_{SD} \leq I_D,$ $T_j = 25\text{ °C}$ |
| Maximum diode commutation speed ³⁾ | di/dt | | | 300 | A/ μ s | (see table 22) |

1) Limited by $T_{j,max}$. Maximum duty cycle $D = 0.75$

2) Pulse width t_p limited by $T_{j,max}$

3) Identical low side and high side switch with identical R_G

3 Thermal characteristics

Table 3 Thermal characteristics TO-220 (IPP60R099C6), TO-247 (IPW60R099C6)

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|------------|--------|------|------|------|---------------------------------------|
| | | Min. | Typ. | Max. | | |
| Thermal resistance, junction - case | R_{thJC} | - | - | 0.45 | °C/W | leaded |
| Thermal resistance, junction - ambient | R_{thJA} | - | - | 62 | | |
| Soldering temperature, wavesoldering only allowed at leads | T_{sold} | - | - | 260 | °C | 1.6 mm (0.063 in.) from case for 10 s |

Table 4 Thermal characteristics TO-220FullIPAK (IPA60R099C6)

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|------------|--------|------|------|------|---------------------------------------|
| | | Min. | Typ. | Max. | | |
| Thermal resistance, junction - case | R_{thJC} | - | - | 3.6 | °C/W | leaded |
| Thermal resistance, junction - ambient | R_{thJA} | - | - | 80 | | |
| Soldering temperature, wavesoldering only allowed at leads | T_{sold} | - | - | 260 | °C | 1.6 mm (0.063 in.) from case for 10 s |

Table 5 Thermal characteristics TO-263 (IPB60R099C6)

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|---|------------|--------|------|------|------|---|
| | | Min. | Typ. | Max. | | |
| Thermal resistance, junction - case | R_{thJC} | - | - | 0.45 | °C/W | SMD version, device on PCB, minimal footprint |
| Thermal resistance, junction - ambient | R_{thJA} | - | - | 62 | | |
| | | - | 35 | - | | |
| Soldering temperature, wave- & reflow soldering allowed | T_{sold} | - | - | 260 | °C | reflow MSL1 |

1) Device on 40mm*40mm*1.5mm one layer epoxy PCB FR4 with 6cm² copper area (thickness 70µm) for drain connection. PCB is vertical without air stream cooling.

4 Electrical characteristics

Electrical characteristics, at $T_J=25\text{ °C}$, unless otherwise specified.

Table 6 Static characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|----------------------------------|---------------|--------|------|-------|---------------|--|
| | | Min. | Typ. | Max. | | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | 600 | - | - | V | $V_{GS}=0\text{ V}$, $I_D=0.25\text{ mA}$ |
| Gate threshold voltage | $V_{GS(th)}$ | 2.5 | 3 | 3.5 | | $V_{DS}=V_{GS}$, $I_D=1.21\text{ mA}$ |
| Zero gate voltage drain current | I_{DSS} | - | - | 5 | μA | $V_{DS}=600\text{ V}$, $V_{GS}=0\text{ V}$, $T_J=25\text{ °C}$ |
| | | - | 50 | - | | $V_{DS}=600\text{ V}$, $V_{GS}=0\text{ V}$, $T_J=150\text{ °C}$ |
| Gate-source leakage current | I_{GSS} | - | - | 100 | nA | $V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$ |
| Drain-source on-state resistance | $R_{DS(on)}$ | - | 0.09 | 0.099 | Ω | $V_{GS}=10\text{ V}$, $I_D=18.1\text{ A}$, $T_J=25\text{ °C}$ |
| | | - | 0.23 | - | | $V_{GS}=10\text{ V}$, $I_D=18.1\text{ A}$, $T_J=150\text{ °C}$ |
| Gate resistance | R_G | - | 1.6 | - | Ω | $f=1\text{ MHz}$, open drain |

Table 7 Dynamic characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|--------------|--------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Input capacitance | C_{iss} | - | 2660 | - | pF | $V_{GS}=0\text{ V}$, $V_{DS}=100\text{ V}$, $f=1\text{ MHz}$ |
| Output capacitance | C_{oss} | - | 154 | - | | |
| Effective output capacitance, energy related ¹⁾ | $C_{o(er)}$ | - | 100 | - | | |
| Effective output capacitance, time related ²⁾ | $C_{o(tr)}$ | - | 500 | - | | $I_D=\text{constant}$, $V_{GS}=0\text{ V}$ $V_{DS}=0\dots480\text{ V}$ |
| Turn-on delay time | $t_{d(on)}$ | - | 15 | - | ns | $V_{DD}=400\text{ V}$, $V_{GS}=13\text{ V}$, $I_D=18.1\text{ A}$, $R_G=1.7\Omega$ (see table 20) |
| Rise time | t_r | - | 12 | - | | |
| Turn-off delay time | $t_{d(off)}$ | - | 75 | - | | |
| Fall time | t_f | - | 6 | - | | |

1) $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$

2) $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$

Table 8 Gate charge characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|-----------------------|---------------|--------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Gate to source charge | Q_{gs} | - | 14 | - | nC | $V_{DD}=480\text{ V}$, $I_D=18.1\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate to drain charge | Q_{gd} | - | 61 | - | | |
| Gate charge total | Q_g | - | 119 | - | | |
| Gate plateau voltage | $V_{plateau}$ | - | 5.4 | - | V | |

Table 9 Reverse diode characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|-------------------------------|-----------|--------|------|------|---------------|--|
| | | Min. | Typ. | Max. | | |
| Diode forward voltage | V_{SD} | - | 0.9 | - | V | $V_{GS}=0\text{ V}$, $I_F=18.1\text{ A}$, $T_j=25\text{ °C}$ |
| Reverse recovery time | t_{rr} | - | 580 | - | ns | $V_R=400\text{ V}$, $I_F=18.1\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$ (see table 22) |
| Reverse recovery charge | Q_{rr} | - | 13 | - | μC | |
| Peak reverse recovery current | I_{rrm} | - | 43 | - | A | |

5 Electrical characteristics diagrams

Table 10

| Power dissipation TO-220, TO-247, TO-263 | Power dissipation TO-220 FullPAK |
|---|-------------------------------------|
| | |
| $P_{tot} = f(T_C)$ | $P_{tot} = f(T_C)$ |

Table 11

| Max. transient thermal impedance TO-220, TO-247, TO-263 | Max. transient thermal impedance TO-220 FullPAK |
|--|--|
| | |
| $Z_{(thJC)} = f(t_p)$; parameter: $D = t_p / T$ | $Z_{(thJC)} = f(t_p)$; parameter: $D = t_p / T$ |

Table 12

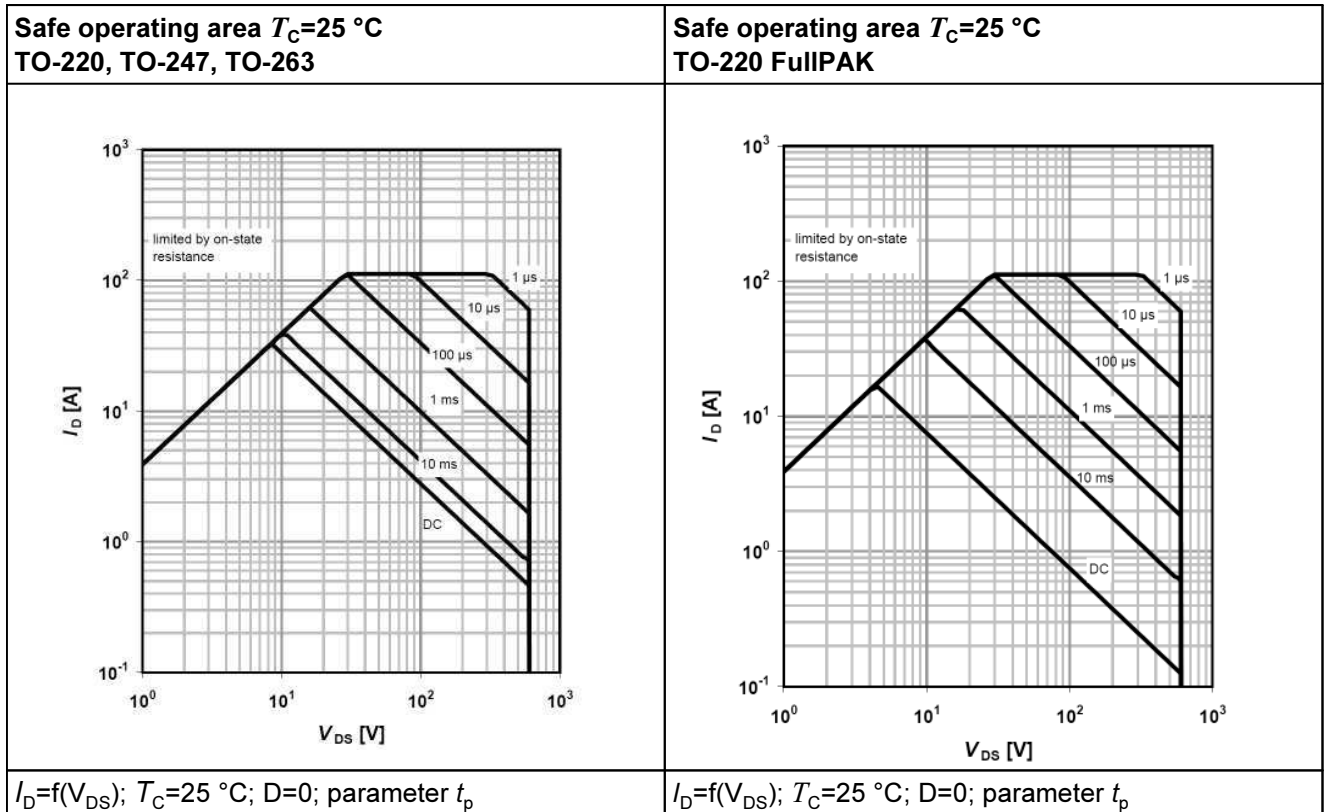


Table 13

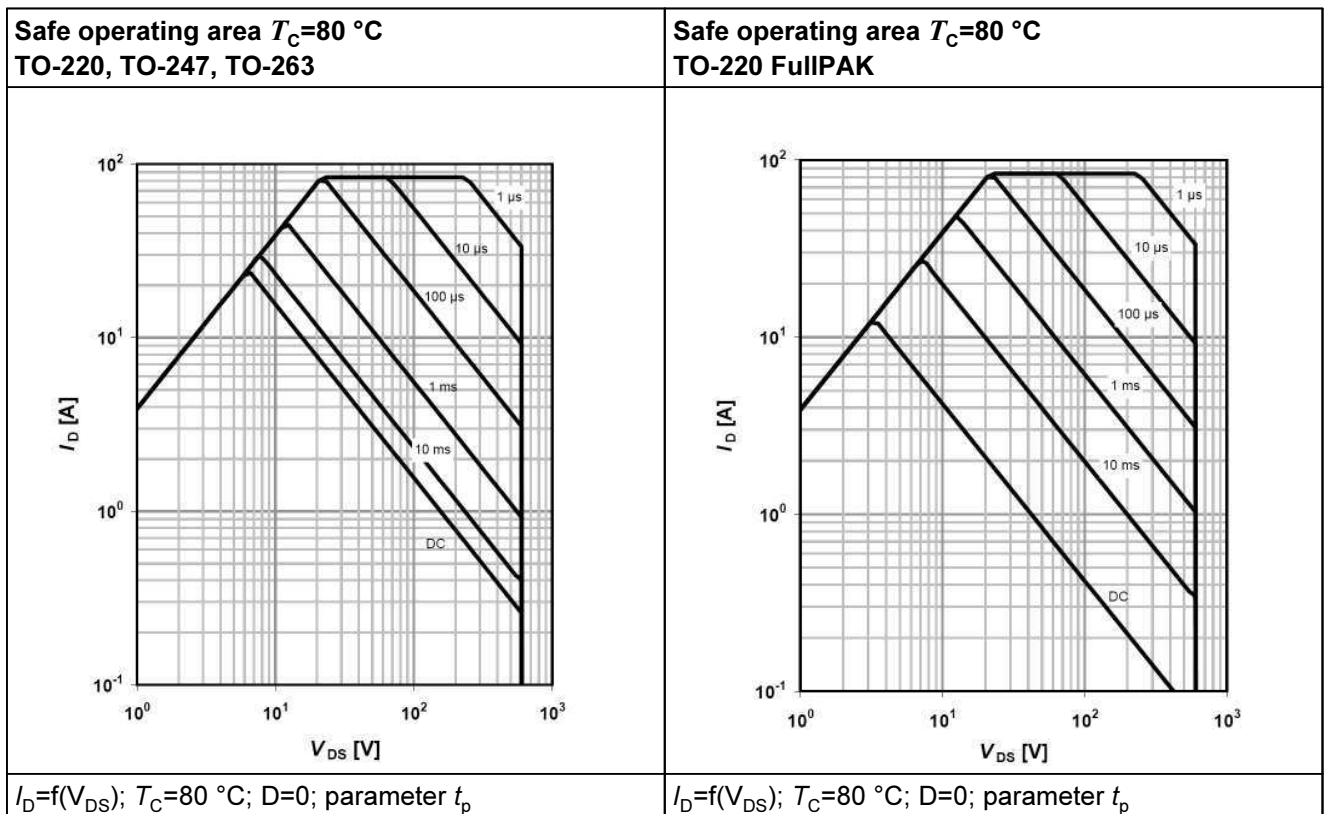


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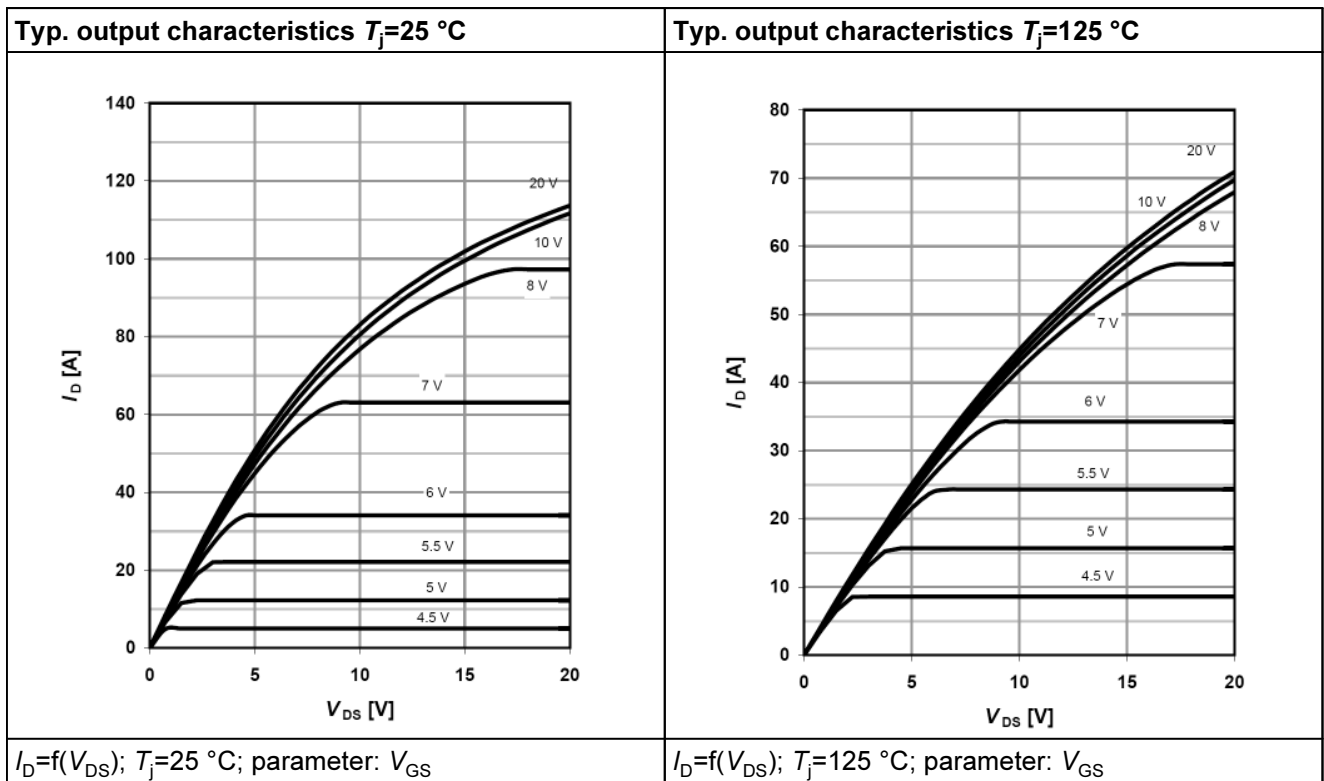


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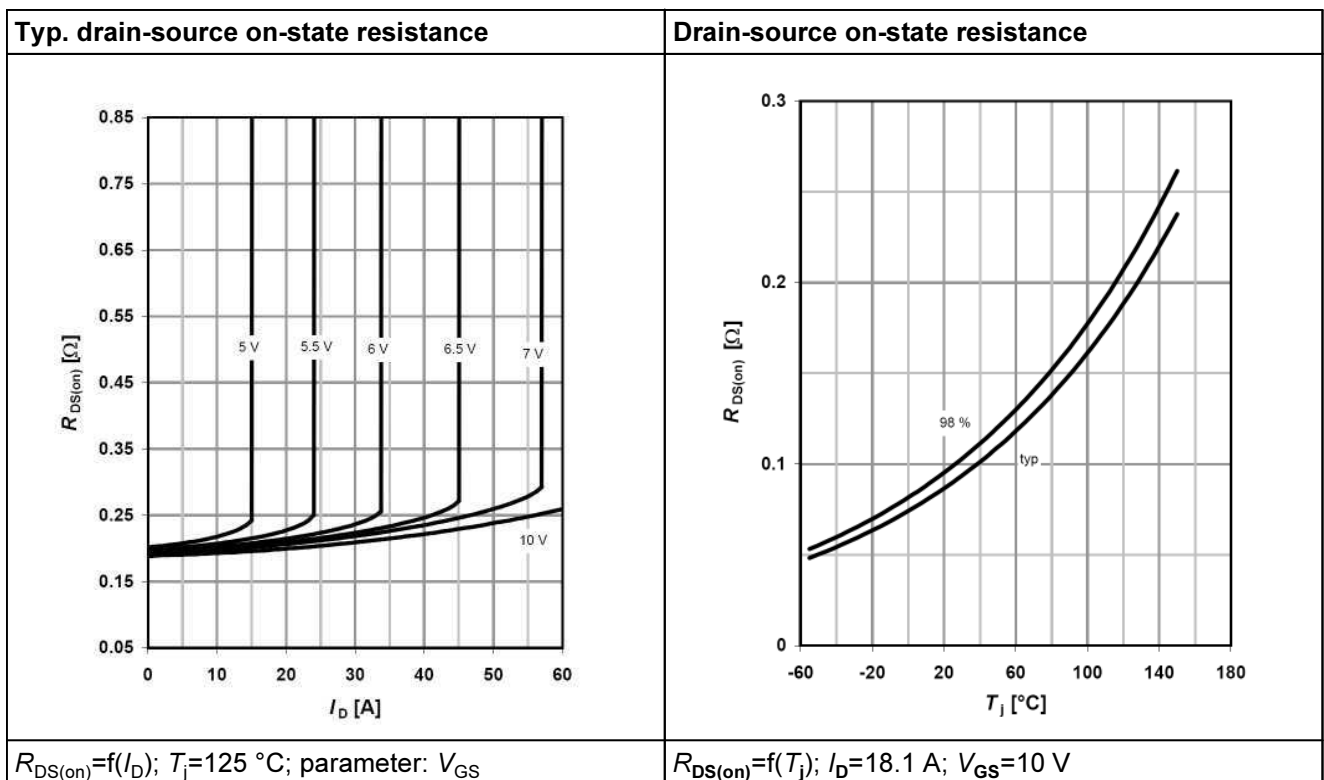


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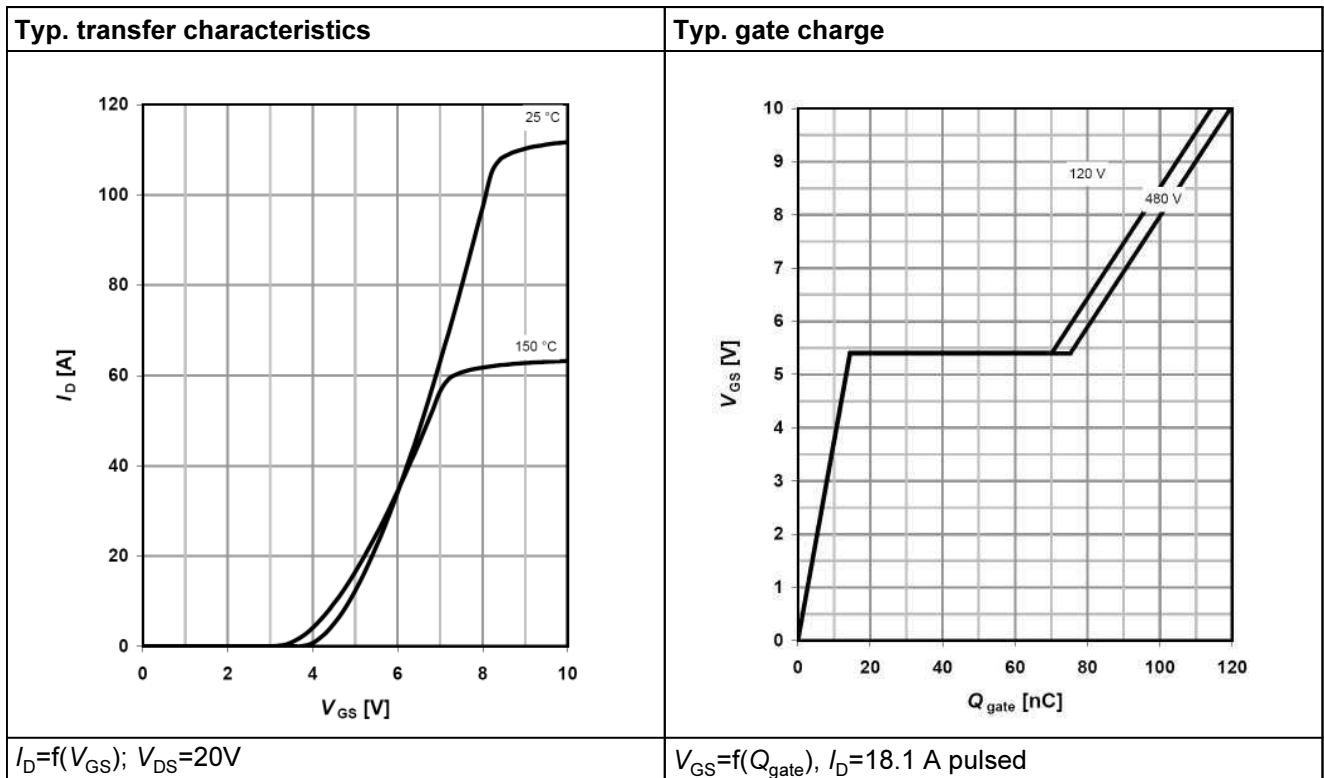


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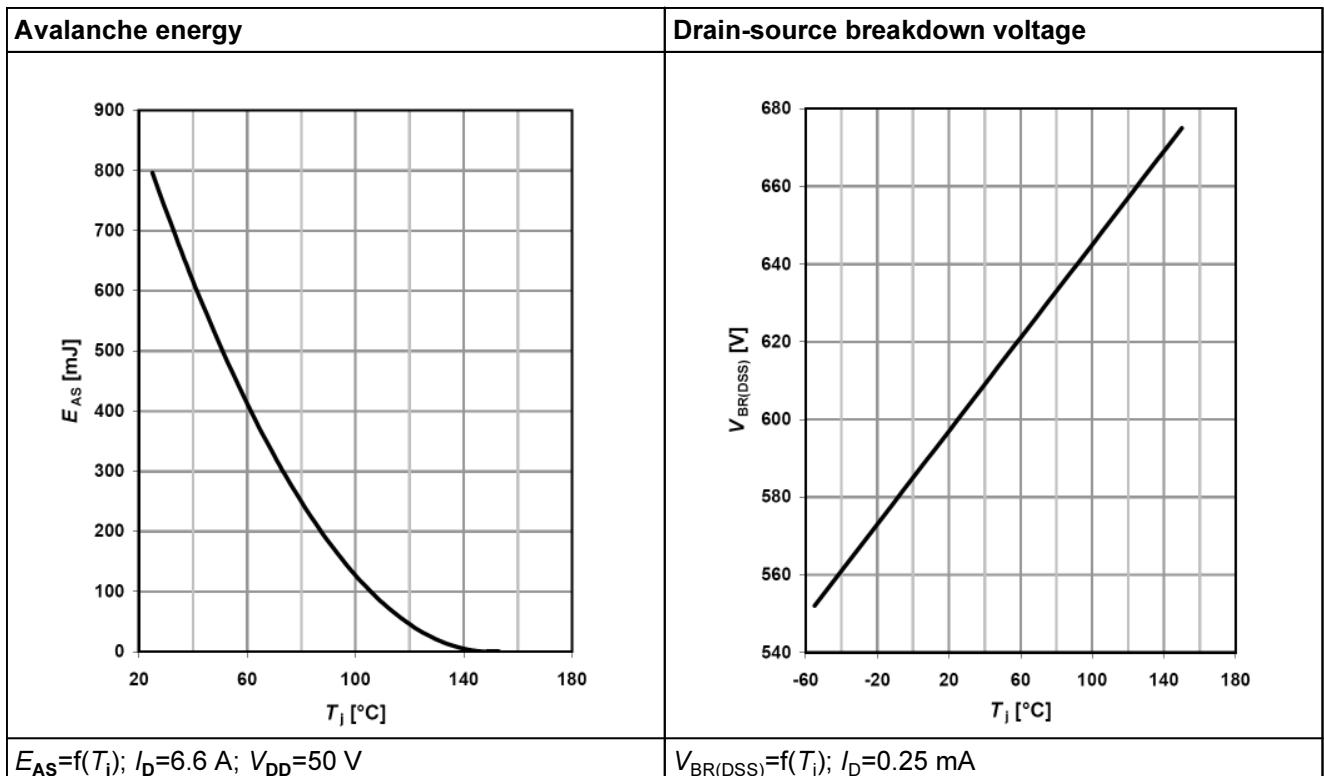


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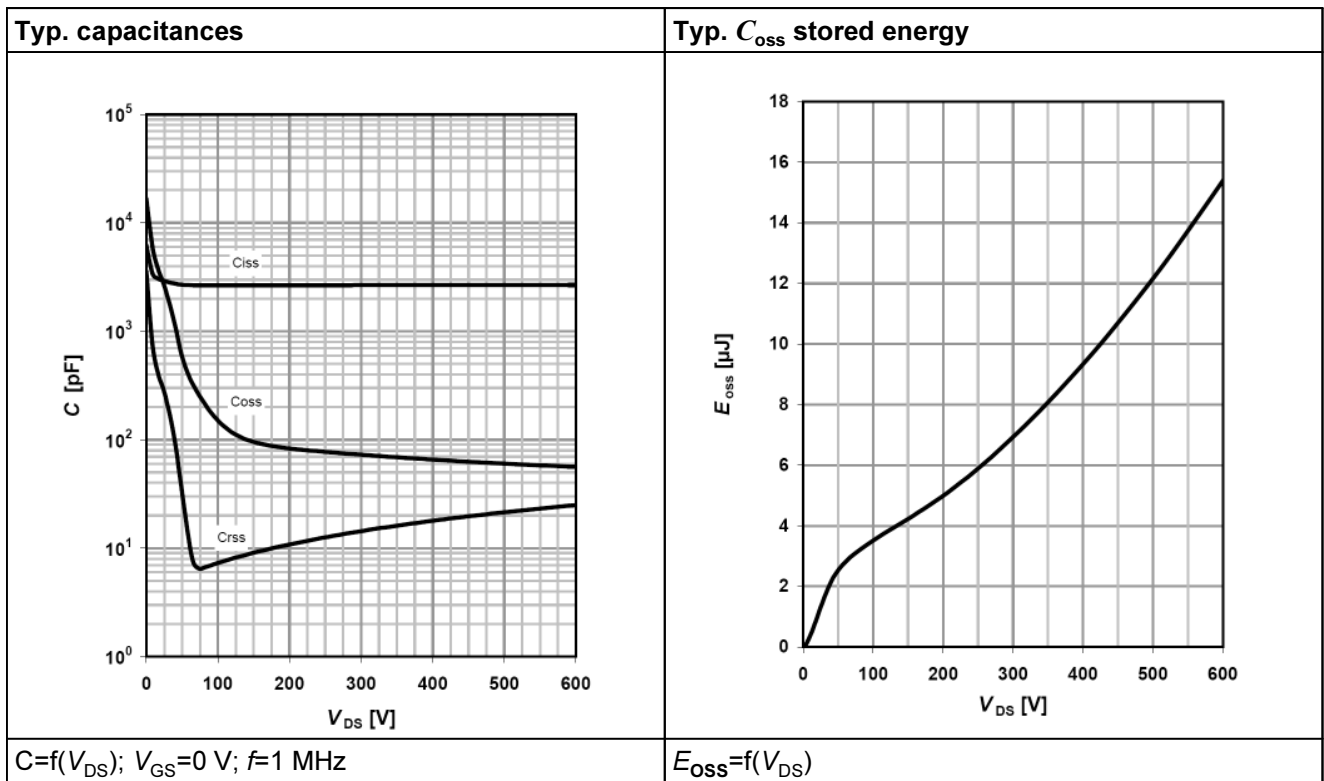
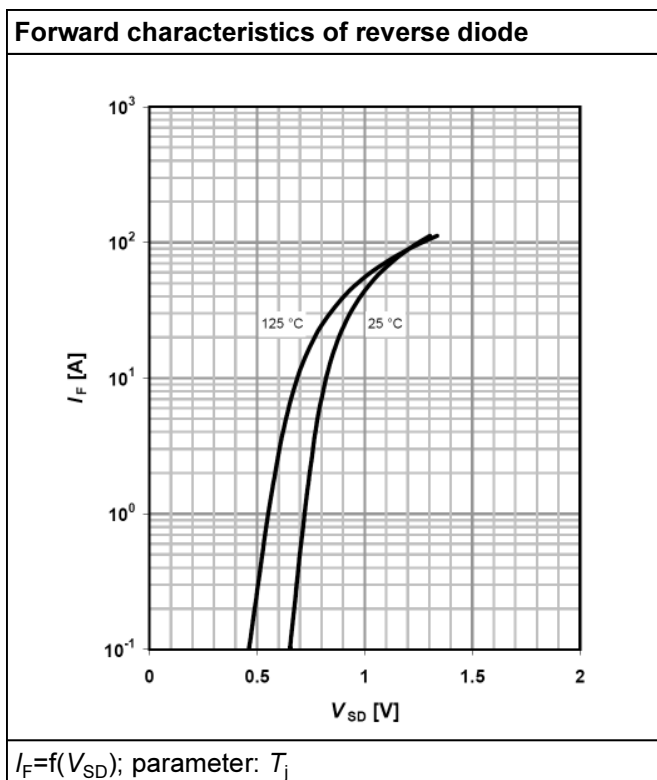


Table 19



7 Package outlines

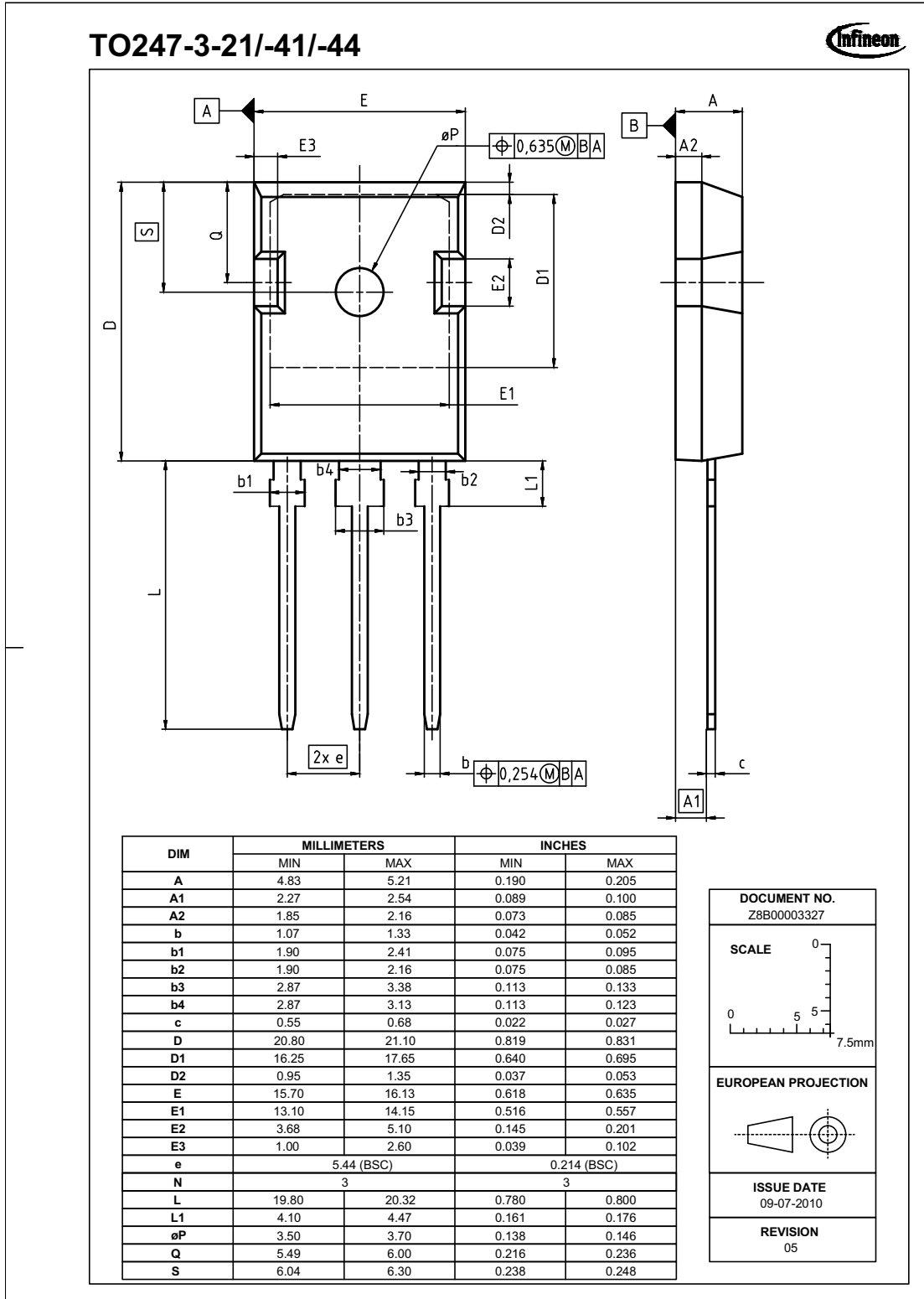
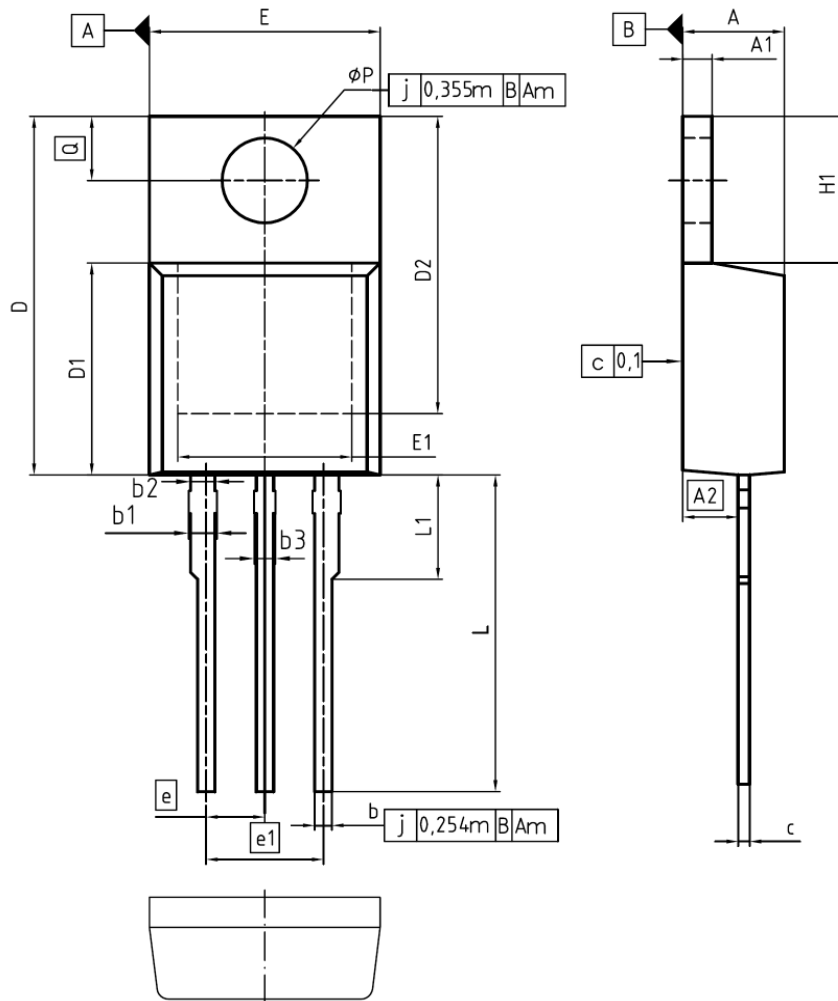


Figure 1 Outlines TO-247, dimensions in mm/inches



| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|-------|--------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.30 | 4.57 | 0.169 | 0.180 |
| A1 | 1.17 | 1.40 | 0.046 | 0.055 |
| A2 | 2.15 | 2.72 | 0.085 | 0.107 |
| b | 0.65 | 0.86 | 0.026 | 0.034 |
| b1 | 0.95 | 1.40 | 0.037 | 0.055 |
| b2 | 0.95 | 1.15 | 0.037 | 0.045 |
| b3 | 0.65 | 1.15 | 0.026 | 0.045 |
| c | 0.33 | 0.60 | 0.013 | 0.024 |
| D | 14.81 | 15.95 | 0.583 | 0.628 |
| D1 | 8.51 | 9.45 | 0.335 | 0.372 |
| D2 | 12.19 | 13.10 | 0.480 | 0.516 |
| E | 9.70 | 10.36 | 0.382 | 0.408 |
| E1 | 6.50 | 8.60 | 0.256 | 0.339 |
| e | 2.54 | | 0.100 | |
| e1 | 5.08 | | 0.200 | |
| N | 3 | | 3 | |
| H1 | 5.90 | 6.90 | 0.232 | 0.272 |
| L | 13.00 | 14.00 | 0.512 | 0.551 |
| L1 | - | 4.80 | - | 0.189 |
| øP | 3.60 | 3.89 | 0.142 | 0.153 |
| Q | 2.60 | 3.00 | 0.102 | 0.118 |

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Figure 2 Outlines TO-220, dimensions in mm/inches

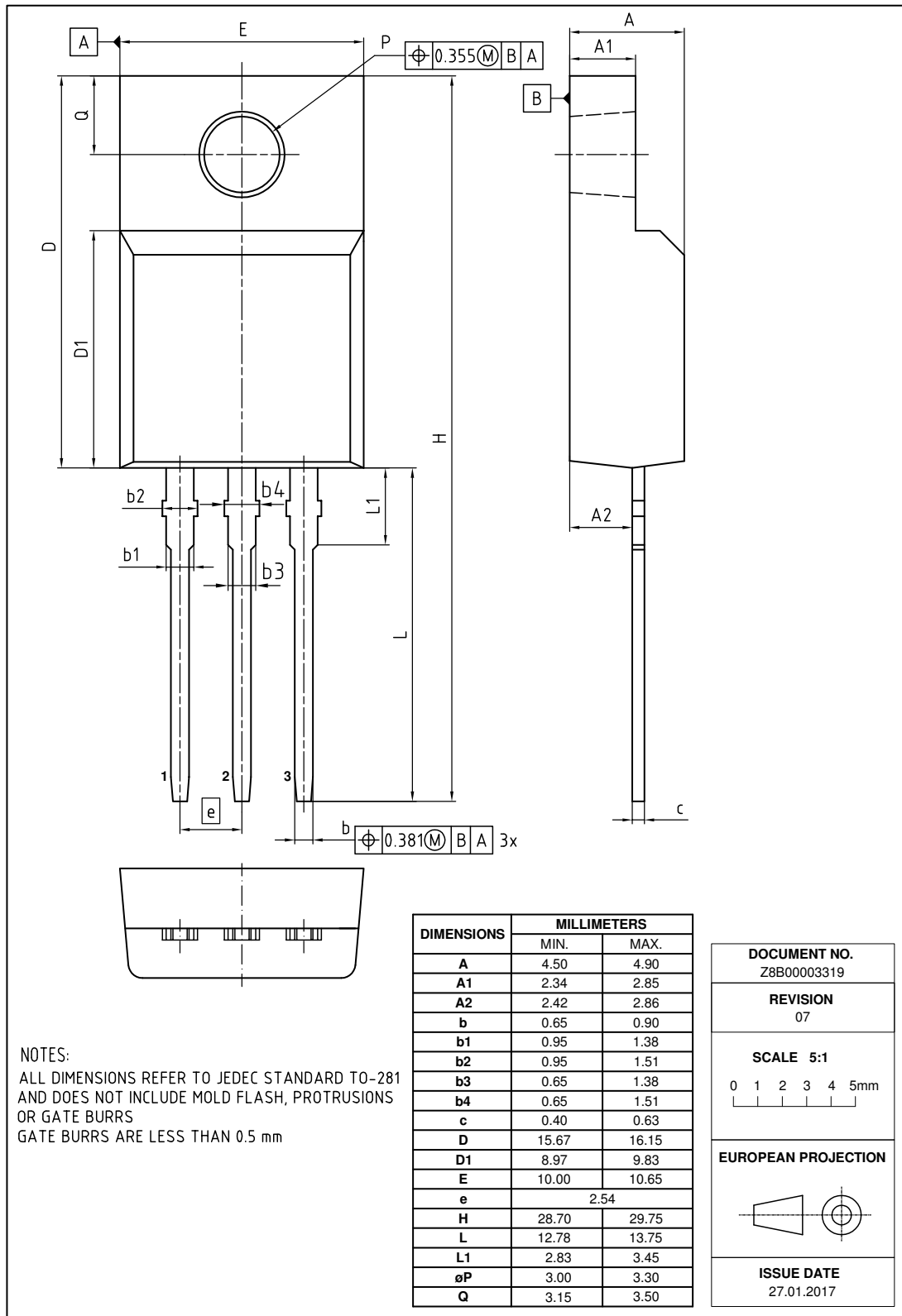


Figure 3 Outline PG-TO-220 FullPAK dimensions in mm

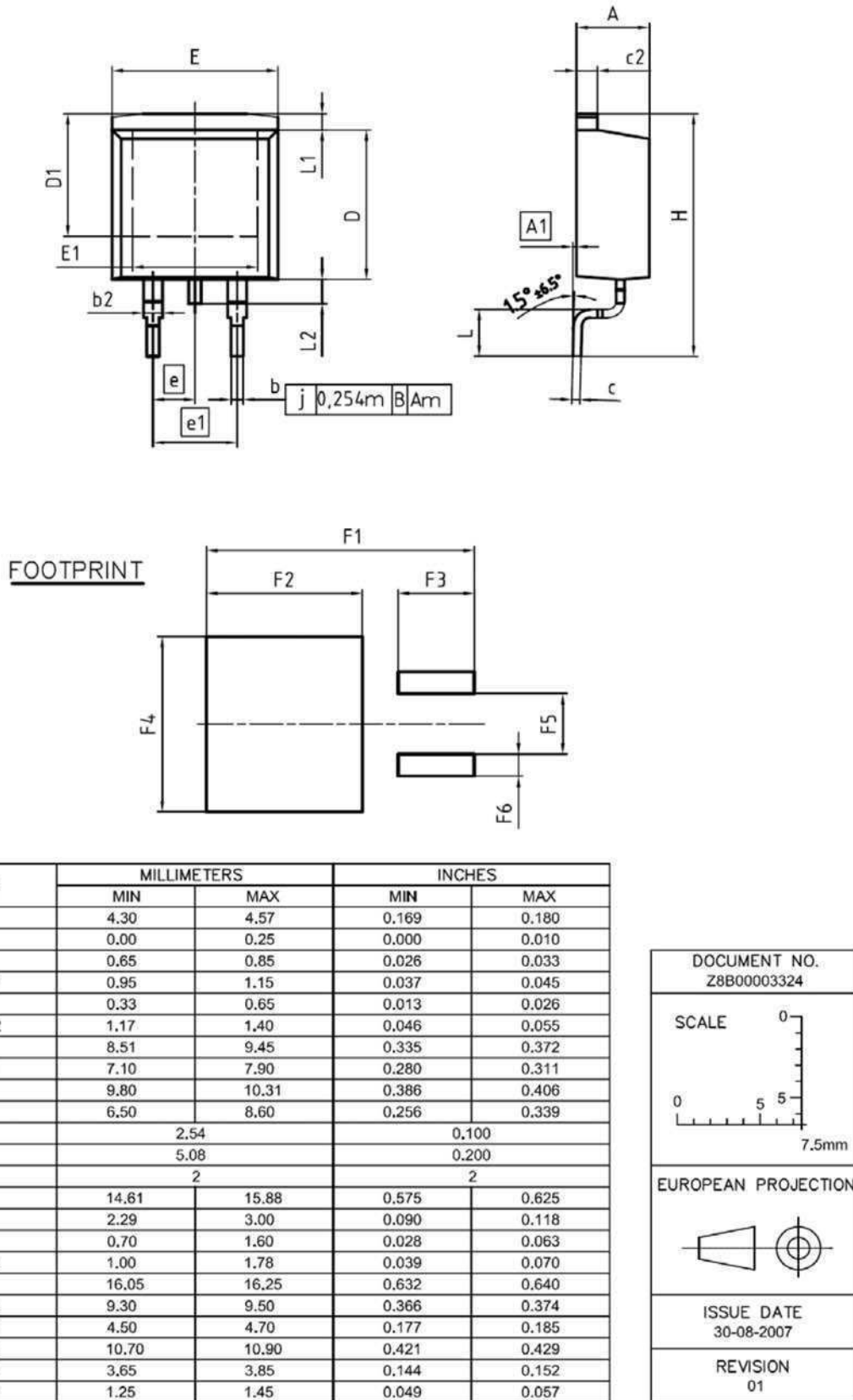


Figure 4 Outlines TO-263, dimensions in mm/inches

600V CoolMOS™ C6 Power Transistor

IPA60R099C6

Revision History

IPA60R099C6

Revision: 2018-03-05, Rev. 2.3

Previous Revision

| Revision | Date | Subjects (major changes since last revision) |
|----------|------------|--|
| 2.3 | 2018-03-05 | Outline PG-TO220 FullPAK update |

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